DATA SHEET



MOS INTEGRATED CIRCUIT μ PD23C128040L

128M-BIT MASK-PROGRAMMABLE ROM 16M-WORD BY 8-BIT (BYTE MODE) / 8M-WORD BY 16-BIT (WORD MODE) PAGE ACCESS MODE

Description

The μ PD23C128040L is a 134,217,728 bits mask-programmable ROM. The word organization is selectable (BYTE mode : 16,777,216 words by 8 bits, WORD mode : 8,388,608 words by 16 bits).

The active levels of OE (Output Enable Input) can be selected with mask-option.

The μ PD23C128040L is packed in 48-pin plastic TSOP(I).

Features

Word organization

16,777,216 words by 8 bits (BYTE mode) 8,388,608 words by 16 bits (WORD mode)

Page access mode

BYTE mode : 8 byte random page access

WORD mode : 4 word random page access

 \bullet Operating supply voltage : Vcc = 3.3 V \pm 0.3 V

Operating supply voltage	Access time / Page access time	Power supply current (Active mode)	Standby current (CMOS level input)
Vcc ns (MAX.)		mA (MAX.)	μΑ (MAX.)
$3.3~\text{V}\pm0.3~\text{V}$	100 / 30	70	30

Ordering Information

Part Number	Package
μPD23C128040LGY-xxx-MJH	48-pin Plastic TSOP(I) (12 x 18) (Normal bent)
μPD23C128040LGY-xxx-MKH	48-pin Plastic TSOP(I) (12 x 18) (Reverse bent)

(xxx : ROM code suffix No.)

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NEC

* Pin Configurations (Marking Side)

/xxx indicates active low signal.

	[μPD23C128040LG1-XXX-WJH]		
	F		
WORD, /BYTE O	1 48	<u> </u>	GND
A16 O	2 47	0	GND
A15 🔾 🗕	3 46	0	O15, A–1
A14 O	4 45	 O	07
A13 🔾 🗕	5 44	-0	O14
A12 〇	6 43	~ 0	O6
A11 〇——►	7 42	0	O13
A10 〇	8 41	0	O5
A9 ()	9 40	 O	O12
A8 ()	10 39	 O	O4
A19 🔾 🛏	11 38	0	Vcc
A21 ()	12 37	0	Vcc
A20 🔾 🗕	13 36	0	A22
A18 〇——►	14 35	 0	O11
A17 ⊖ ►	15 34	 0	O3
A7 ()	16 33	 0	O10
A6 O	17 32	 0	O2
A5 O	18 31	 O	O9
A4 O	19 30	~~ O	01
A3 ()	20 29	 0	O8
A2 ◯	21 28	~~ O	O0
A1 O	22 27	0	/OE, OE, DC
A0 O	23 26	0	GND
/CE O	24 25		GND
		1	

48-pin plastic TSOP(I) (12 x 18) (Normal bent)

[µPD23C128040LGY-xxx-MJH]

A0 - A22	: Address inputs
00 - 07, 08 - 014	: Data outputs
O15, A–1	: Data output 15 (WORD mode),
	LSB Address input (BYTE mode)
WORD, /BYTE	: Mode select
/CE	: Chip Enable
/OE, OE	: Output Enable
Vcc	: Supply voltage
GND	: Ground
DC	: Don't Care

Remark Refer to Package Drawings for the 1-pin index mark.

Data Sheet M13643EJ4V0DS

	48 1		WORD, /BYTE
	47 2		A16
015, A–1 	46 3		A15
07 🖂	45 4		A14
014 _	44 5		A13
O6 🔾 🗕	43 6		A12
013 _	42 7		A11
O5 🕞 🗕	41 8		A10
012 () -	40 9	0	A9
04 🕞	39 10		A8
Vcc ()	38 11		A19
Vcc O	37 12		A21
A22 🔿 🗕 🕨	36 13		A20
011 O -	35 14		A18
O3 🔾 🗕	34 15		A17
O10 ⊖ -	33 16		A7
02 🖂	32 17		A6
O9 🔾 🗕	31 18		A5
01 🖂	30 19		A4
O8 🔾 🗕	29 20		A3
O0)-	28 21		A2
/OE, OE, DC ○	27 22		A1
	26 23		A0
GND O	25 24		/CE
		1	

48-pin plastic TSOP(I) (12 x 18) (Reverse bent)

[µPD23C128040LGY-xxx-MKH]

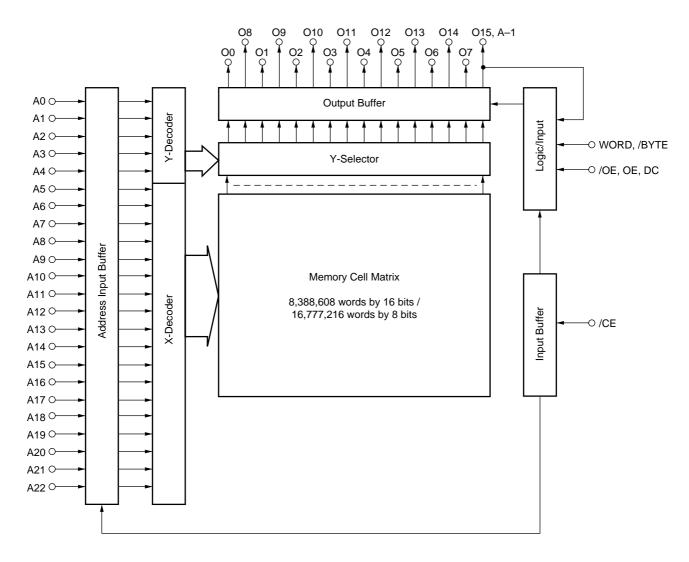
A0 - A22	: Address inputs
00 - 07, 08 - 014	: Data outputs
O15, A–1	: Data output 15 (WORD mode),
	LSB Address input (BYTE mode)
WORD, /BYTE	: Mode select
/CE	: Chip Enable
/OE, OE	: Output Enable
Vcc	: Supply voltage
GND	: Ground
DC	: Don't Care

Remark Refer to **Package Drawings** for the 1-pin index mark.

Input / Output Pin Functions

Pin name	Input / Output	Function		
WORD, /BYTE	Input	The pin for switching WORD mode and BYTE mode.		
		High level : WORD mode (8M-word by 16-bit)		
		Low level : BYTE mode (16M-word by 8-bit)		
A0 to A22	Input	Address input pins.		
(Address inputs)		A0 to A22 are used differently in the WORD mode and the BYTE mode.		
		WORD mode (8M-word by 16-bit)		
		A0 to A22 are used as 23 bits address signals.		
		BYTE mode (16M-word by 8-bit)		
		A0 to A22 are used as the upper 23 bits of total 24 bits of address signal.		
		(The least significant bit (A–1) is combined to O15.)		
O0 to O7, O8 to O14	Output	Data output pins.		
(Data outputs)		O0 to O7, O8 to O14 are used differently in the WORD mode and the BYTE mode.		
		WORD mode (8M-word by 16-bit)		
		The lower 15 bits of 16 bits data outputs to O0 to O14.		
		(The most significant bit (O15) combined to A–1.)		
		BYTE mode (16M-word by 8-bit)		
		8 bits data outputs to O0 to O7 and also O8 to O14 are high impedance.		
O15, A–1	Output, Input	O15, A-1 are used differently in the WORD mode and the BYTE mode.		
(Data output 15,		WORD mode (8M-word by 16-bit)		
LSB Address input)		The most significant output data bus (O15).		
		BYTE mode (16M-word by 8-bit)		
		The least significant address bus (A-1).		
/CE	Input	Chip activating signal.		
(Chip Enable)		When the OE is active, output states are following.		
		High level : High impedance		
		Low level : Data out		
/OE, OE, DC	Input	Output enable signal. The active level of OE is mask option. The active level of OE		
(Output Enable, Don't Care)		can be selected from high active, low active and Don't care at order.		
Vcc	_	Supply voltage		
GND	-	Ground		

Block Diagram



Mask Option

The active levels of output enable pin (/OE, OE, DC) are mask programmable and optional, and can be selected from among " 0 " " 1 " " x " shown in the table below.

Option	/OE, OE, DC	OE active level
0	/OE	L
1	OE	Н
x	DC	Don't care

Operation modes for each option are shown in the tables below.

Operation mode (Option : 0)

/CE	/OE	Mode	Output state
L	L	Active	Data out
	Н		High impedance
н	H or L	Standby	High impedance

Operation mode (Option : 1)

/CE	OE	Mode	Output state
L	L	Active	High impedance
	Н		Data out
н	H or L	Standby	High impedance

Operation mode (Option : x)

	/CE	DC	Mode	Output state
ſ	L	H or L	Active	Data out
I	Н	H or L	Standby	High impedance

Remark L: Low level input

H : High level input

Electrical Specifications

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Supply voltage	Vcc		-0.3 to +4.6	V
Input voltage	Vı		–0.3 to Vcc+0.3	V
Output voltage	Vo		–0.3 to Vcc+0.3	V
Operating ambient temperature	TA		-10 to +70	°C
Storage temperature	Tstg		-65 to +150	°C

Caution Exposing the device to stress above those listed in Absolute Maximum Ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Capacitance (TA = 25°C)

Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit
Input capacitance	С	f = 1 MHz			10	pF
Output capacitance	Co				12	pF

DC Characteristics (T_A = -10 to +70°C, V_{CC} = 3.3 V \pm 0.3 V)

Parameter	Symbol	Test conditions	MIN.	TYP.	MAX.	Unit
High level input voltage	Vін		2.2		Vcc + 0.3	V
Low level input voltage	VIL		-0.3		+0.8	V
High level output voltage	Vон	Іон = -100 μА	2.4			V
Low level output voltage	Vol	lo∟ = 2.1 mA			0.4	V
Input leakage current	lu	$V_1 = 0 V$ to V_{CC}	-10		+10	μA
Output leakage current	Ilo	Vo = 0 V to Vcc, Chip deselected	-10		+10	μA
Power supply current	Icc1	/CE = VIL (Active mode), Io = 0 mA			70	mA
Standby current	Іссз	/CE = Vcc - 0.2 V (Standby mode)			30	μA

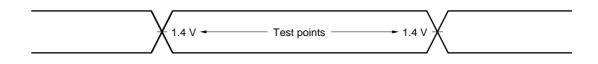
AC Characteristics (T_A = -10 to +70°C, V_{CC} = 3.3 V ± 0.3 V)

Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit
Address access time	tacc				100	ns
Page access time	t PAC				30	ns
Chip enable access time	tce				100	ns
Output enable access time	toe				30	ns
Output hold time	tон		0			ns
Output disable time	t DF		0		25	ns
WORD, /BYTE access time	twв				100	ns

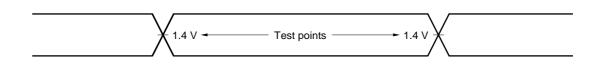
Remark toF is the time from inactivation of /CE or /OE, OE to high-impedance state output.

AC Test Conditions

Input waveform (Rise / Fall time ≤ 5 ns)



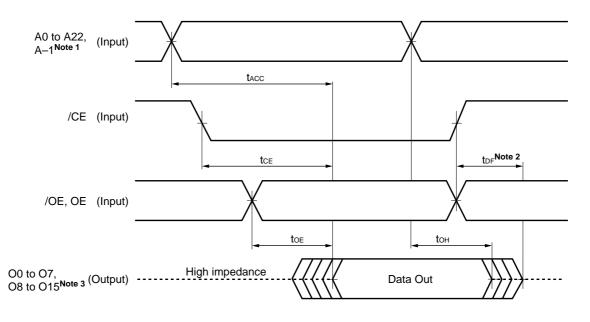
Output waveform



Output load

1TTL + 100 pF

Read Cycle Timing Chart 1

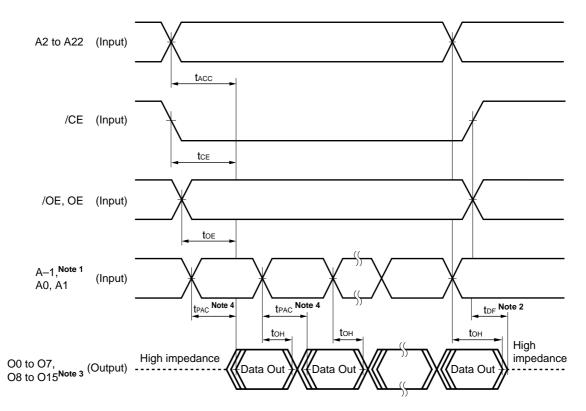


Notes 1. During WORD mode, A-1 is O15.

2. tDF is specified when one of /CE, /OE, OE is inactivated.

3. During BYTE mode, O8 to O14 are high impedance and O15 is A-1.

* Read Cycle Timing Chart 2 (Page Access Mode)

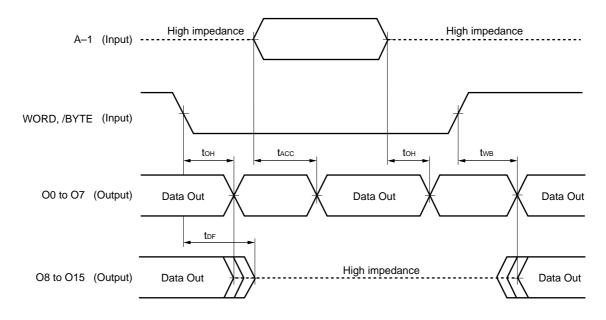


Notes 1. During WORD mode, A–1 is O15.

- **2.** t_{DF} is specified when one of /CE, /OE, OE is inactivated.
- 3. During BYTE mode, O8 to O14 are high impedance and O15 is A-1.
- 4. The definition of page access time is as follows.

Page access time	Upper address (A2 to A22)	/CE input condition	/OE, OE input condition
	inputs condition		
t pac	Before tacc – tpac	Before tce - tPAC	Before stabilizing of page
			address (A-1, A0, A1)

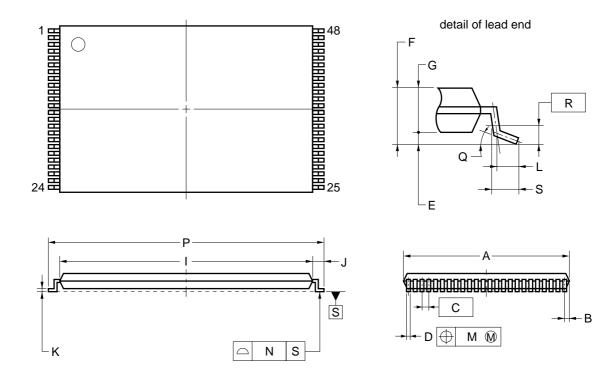
WORD, /BYTE Switch Timing Chart



Remark /OE, OE and /CE : Active.

* Package Drawings

48-PIN PLASTIC TSOP(I) (12x18)



NOTES

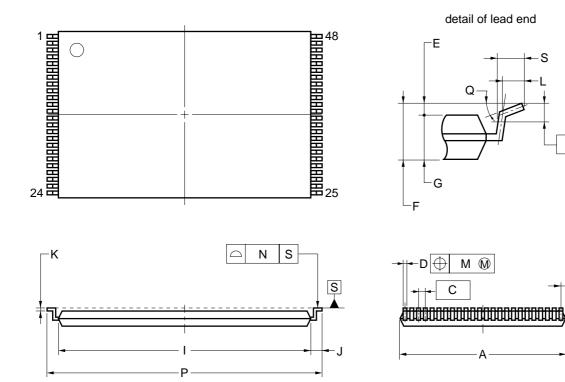
- 1. Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.
- 2. "A" excludes mold flash. (Includes mold flash : 12.4 mm MAX.)

ITEM	MILLIMETERS
Α	12.0±0.1
В	0.45 MAX.
С	0.5 (T.P.)
D	0.22±0.05
Е	0.1±0.05
F	1.2 MAX.
G	1.0±0.05
1	16.4±0.1
J	0.8±0.2
К	0.145±0.05
L	0.5
М	0.10
N	0.10
Р	18.0±0.2
Q	3° ^{+5°} -3°
R	0.25
S	0.60±0.15
	S48GY-50-MJH1-1

R

⊢В

48-PIN PLASTIC TSOP(I) (12x18)



NOTES

- 1. Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.
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ITEM	MILLIMETERS
А	12.0±0.1
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E	0.1±0.05
F	1.2 MAX.
G	1.0±0.05
I	16.4±0.1
J	0.8±0.2
К	0.145±0.05
L	0.5
М	0.10
N	0.10
Р	18.0±0.2
Q	$3^{\circ}^{+5^{\circ}}_{-3^{\circ}}$
R	0.25
S	0.60±0.15
S	648GY-50-MKH1-1

Recommended Soldering Conditions

Please consult with our sales offices for soldering conditions of the μ PD23C128040L.

Types of Surface Mount Device

μ PD23C128040LGY-MJH	: 4	48-pin plastic TSOP(I) (12 x 18) (Normal bent)
μPD23C128040LGY-MKH	: 4	48-pin plastic TSOP(I) (12 x 18) (Reverse bent)

NOTES FOR CMOS DEVICES -

① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

(2) HANDLING OF UNUSED INPUT PINS FOR CMOS

Note:

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

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